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# SUPPORTING INFORMATION FILE

# Thermoelectric properties of $In_1Co_4Sb_{12+\delta}$ : role of *in situ* formed InSb precipitates, Sb overstoichiometry, and processing conditions

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# Scheme of the fabrication route for the samples under study



**Figure S1.** Schematic illustration of the fabrication routes for the In-filled skutterudites with a nominal composition of  $In_1Co_4Sb_{12+\delta}$ . Here IM is the induction melting, AN is the annealing, BM is the ball milling, MS is the melt spinning, and SPS is the spark plasma sintering.

#### XRD data for all the samples before sintering



**Figure S2.** PXRD patterns for the samples with a nominal composition of  $In_1Co_4Sb_{12+\delta}$  before spark plasma sintering after (a) induction melting and ball milling (IM + BM), induction melting, annealing and ball milling (IM + A + BM), (b) induction melting and melt spinning (IM + MS), induction melting, annealing and melt spinning (IM + A + MS). Bragg's reflections for the CoSb<sub>3</sub> phase are indicated by ticks on the top part of the figure. The first and the second sets of samples were obtained by sintering the powders whose XRD patterns are shown in (a). The third set of samples was fabricated by sintering the ribbons whose XRD patterns are shown in (b).

**Table S1.** The phase composition of the samples with a nominal composition of  $In_1Co_4Sb_{12+\delta}$  before spark plasma sintering according to the XRD pattern refinement.

		Route*						
Phase	IM + BM		IM + A + BM		IM + MS		IM + A + MS	
	Content (vol.%)	Lattice parameters (Å)						
CoSb₃	5.7	<i>a</i> = 9.042	80.3	<i>a</i> = 9.051	0	n/a	3.6	<i>a</i> = 9.050
		a = 5.577				a = 5.587		a = 5.588
CoSb <sub>2</sub>	27.8	b = 6.385	0	n/a	40.9	<i>b</i> = 6.391	41.7	<i>b</i> = 6.391
		<i>c</i> = 3.375				<i>c</i> = 3.367		<i>c</i> = 3.369
CoSb	9.5	a = 3.869	0	n/a	15.7	<i>a</i> = 3.852	12.3	a = 3.853
		<i>c</i> = 5.194				<i>c</i> = 5.202		<i>c</i> = 5.200
InSb	14.8	<i>a</i> = 6.475	17.2	<i>a</i> = 6.479	4.6	<i>a</i> = 6.466	5.7	<i>a</i> = 6.465
Sb	42.2	a = 4.296 c = 11.298	2.5	-	38.8	a = 4.279 c = 11.316	36.7	a = 4.279 c = 11.318

\*According to labels depicted in Figure S2.

#### **Rietveld refinements**



**Figure S3.** Rietveld refinements for the (a) BMG, (b) BMAG, (c) MS, (d) MSA, (e) BM, and (f) BMA samples after spark plasma sintering and annealing. Bragg's reflections for the CoSb<sub>3</sub> phase are indicated by ticks on the top part of the figure.

**Table S2.** Reliability factors of the refined spectra shown in Fig. S3: intensity *R*-factor,  $R_p$ , weighted profile *R*-factor,  $R_{wp}$ , expected *R*-factor,  $R_{exp}$ , and goodness of fit, *GoF* (= $R_{wp}/R_{exp}$ ).

$$\operatorname{Here} R_{de} = \frac{\max(y_{obs,i} - y_{colc,i})}{\max(y_{obs,i})}, R_{p} = \frac{\sum_{i=1}^{N} |y_{obs,i} - y_{colc,i}|}{\sum_{i=1}^{N} y_{obs,i}}, R_{wp} = \sqrt{\frac{\sum_{i=1}^{N} w_{i}(y_{obs,i} - y_{colc,i})^{2}}{\sum_{i=1}^{N} w_{i}y_{obs,i}^{2}}}, \text{ and } R_{exp} = \sqrt{\frac{N-P}{\sum_{i=1}^{N} w_{i}y_{obs,i}^{2}}}, \text{ where } y_{obs,i} \text{ is the } y_{obs,i} \text{ is } y_{obs,i} \text{ is the } y_{obs,i} \text{ is the } y_{obs,i} \text{ is } y_{obs$$

observed (experimental) intensity,  $y_{calc,i}$  is the calculated intensity,  $w_i$  is the weight, N is the number of data points, and P is the number of refined parameters (for all the samples  $P \approx 20$  and thus  $N \gg P$ ).

Table S3. Crystal structure data for all the phases mentioned in this study (Fig. 1, Fig. S2)	).

Phase	Pearson symbol	Space group	Structure type	Structure type in Strukturbericht notation	PDF card number
CoSb₃	cl32	_ Im3	As <sub>3</sub> Co	D0 <sub>2</sub>	65-3144
$CoSb_2$	oP6	Pnnm	FeS <sub>2</sub>	C18	89-4869
CoSb	hP4	P6 <sub>3</sub> /mmc	NiAs	B81	65-8979
InSb	cF8	_ F43m	ZnS	В3	65-4817
Sb	hR2	_ R3m	αAs	Α7	76-8600

#### **EBSD** analysis



Figure S4. EBSD microstructures of the In<sub>1</sub>Co<sub>4</sub>Sb<sub>12+δ</sub> samples prepared by various methods: (a – d) band contrast images; (e – j) phase contrast images with CoSb<sub>3</sub> phase in pale blue color, InSb in black and CoSb<sub>2</sub> in red color; (i – m) orientational contrast images for BMG (a, e, i), BMAG (b, f, k), MS (c, g, I), and MSA (d, j, m) samples, respectively.

**Table S4.** Calculated from the EBSD data average grain size  $D_g$  and grain boundaries length *GB* for the In<sub>1</sub>Co<sub>4</sub>Sb<sub>12+ $\delta$ </sub> samples prepared by various methods.

Droparty	Samples' codes				
Property	BMG	BMAG	MS	MSA	
Average grain size D <sub>g</sub> (μm)	6.0	20.3	9.6	10.4	
Grain boundaries length GB (µm)	23738	8401	9452	8956	

# SEM images of the fracture surfaces



Figure S5. SEM images of the fracture surfaces of the (a) BMG, (b) BMAG, (c) BM, (d) BMA, (e) MS, and (f) MSA samples after spark plasma sintering and annealing.

#### EDX mapping for the BMG and BMAG samples



25 µm

**Figure S6.** SEM image of the polished surface of the BMG specimen and corresponding EDX maps of the area indicated by the white rectangle. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.



25 µm

**Figure S7.** SEM image of the polished surface of the BMAG specimen and corresponding EDX maps of the area indicated by the white rectangle. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.



## Electron diffraction patterns and representative EDX spectrum for the precipitates shown in Fig. 2c,f

**Figure S8.** (a, b) Indexed electron diffraction patterns for the precipitates shown in Fig. 2c and (c) representative EDX spectrum of the inclusions shown in Fig. 2f in the main text.

#### EDX mapping for the BM and BMA samples



**Figure S9.** SEM image of the polished surface of the BM specimen and corresponding EDX maps. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.



Figure S10. SEM image of the polished surface of the BMA specimen and corresponding EDX maps. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.

#### EDX mapping for the MS and MSA samples



25 µm

**Figure S11.** SEM image of the polished surface of the MS specimen and corresponding EDX maps of the area indicated by the white rectangle. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.



25 µm

**Figure S12.** SEM image of the polished surface of the MSA specimen and corresponding EDX maps of the area indicated by the white rectangle. SEM micrograph in electron channeling contrast mode is also shown in the lower right corner.

#### Thermoelectric properties; comparison with previous reports



**Figure S13.** (a) Electrical conductivity,  $\sigma$ , (b) Seebeck coefficient,  $\alpha$ , (c) total thermal conductivity,  $\kappa_{tot}$ , and (d) figure of merit, zT, for the  $\ln_1 \text{Co}_4 \text{Sb}_{12+\delta}$  obtained in this work (MSA route) and for other In-filled  $\text{CoSb}_3$  skutterudites presented for comparison.<sup>1–14</sup>

#### Field and angular dependencies of the Hall resistance



**Figure S14.** Magnetic field dependence of the Hall resistance for the (a) BMG, (b) BMAG, (c) MS, (d) MSA, (e) BM, and (f) BMA samples. Empty symbols are the experimentally measured points; black dashed lines are the linear fit. Here,  $R_{\rm H}$  is determined from the slope of the obtained line.



**Figure S15.** Angular dependence of the Hall resistance in a magnetic field of 1 T for the (a) BMG, (b) BMAG, (c) MS, (d) MSA, (e) BM, and (f) BMA samples. Empty symbols are the experimentally measured points; black dashed lines are the fit with harmonic sine law  $\rho_{\rm H} (\varphi) = \rho_{\rm H0} + \rho_{\rm H1} \sin(\varphi - \varphi_0)$ ,  $R_{\rm H} = \rho_{\rm H1}/H$ .

## Charge carrier concentration and mobility; comparison with previous reports



**Figure S16.** (a) Carrier concentration, *n*, and (b) carrier mobility,  $\mu$ , as a function of actual In content in the Co<sub>4</sub>Sb<sub>12</sub> matrix. (c) Seebeck coefficient,  $\alpha$ , and (d) carrier mobility,  $\mu$ , as a function of charge carrier concentration. The orange crosses represent data for the In<sub>1</sub>Co<sub>4</sub>Sb<sub>12+ $\delta$ </sub> samples obtained in this work (MS, MSA, BMG, and BMAG routes) and for other In-filled CoSb<sub>3</sub> skutterudites presented here for comparison.<sup>2,4,8,11,15-17</sup> Black dashed lines are the guides for the eye.

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